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TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74HC4060AP, TC74HC4060AF

14 – STAGE BINARY COUNTER / OSCILATOR

The TC74HC4060A is a high speed CMOS 14 - STAGE BINARY COUNTER fabricated with silicon gate C^2MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation. The oscillator configuration allows designs using either RC or crystal oscillator circuits, or an external clock may be used. The clear input resets the counter to a low level on all outputs and disables the oscillator.

A high CLR accomplishes this reset function.

A negative transition on the clock input $(\overline{\phi}I)$ increments the counter Ten levels of divided output are provided; 4 stage thru 10 stage and 12 stage thru 14 stage. At the last stage (Q14), a 1/16384 divided frequency is obtained.

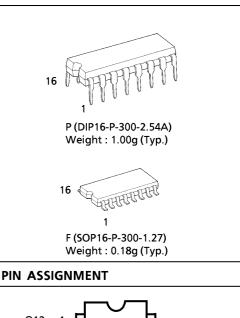
The $\overline{\phi}I$ input and CLR input are equipped with protection circuits against static discharge or transient excess voltage.

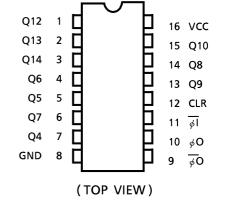
FEATURES:

- High Speed------f_{MAX} = 58MHz (typ.) at V_{CC} = 5V
- Low Power Dissipation $I_{CC} = 4\mu A$ (Max.)at Ta = 25°C
- High Noise Immunity $V_{\text{NIH}} = V_{\text{NIH}} = 28\% V_{\text{CC}}$ (Min.)
- Output Drive Capability 10 LSTTL Loads
- Symmetrical Output Impedance... $|I_{OH}| = I_{OL} = 4mA(Min.)$
- Balanced Propagation Delays $\cdots t_{pLH} \simeq t_{pHL}$
- Wide Operating Voltage Range \cdots V_{CC} (opr.) = 2V ~ 6V
- Oscillator Configuration RC or Crystal Oscillator
- Pin and Function Compatible with 4060B

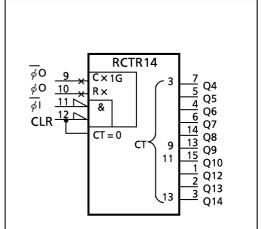
TRUTH TABLE

INP	UTS	FUNCTION					
٥	CLR	FUNCTION					
х	н	Counter is reset to zero state.					
7	L	Count up one step.					
	L	No change					





IEC LOGIC SYMBOL



980508EBA2

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TOSHIBA

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V _{cc}	-0.5~7	V
DC Input Voltage	VIN	$-0.5 \sim V_{CC} + 0.5$	V
DC Output Voltage	V _{OUT}	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	Ι _{ικ}	± 20	mA
Output Diode Current	Ι _{οκ}	± 20	mA
DC Output Current	I _{OUT}	± 25	mA
DC V _{CC} /Ground Current	I _{CC}	± 50	mA
Power Dissipation	P _D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T _{stg}	-65~150	°C

*500mW in the range of Ta = -40°C~65°C. From Ta = 65°C to 85°C a derating factor of -10mW/°C shall be applied write 200mW until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT					
Supply Voltage	V _{cc}	2~6	V					
Input Voltage	VIN	0~V _{CC}	V					
Output Voltage	V _{OUT}	0~V _{CC}	V					
Operating Temperature	T _{opr}	-40~85	°C					
Input Rise and Fall Time	t _r , t _f	$\begin{array}{l} 0 \sim 1000 \ (V_{CC} = 2.0V) \\ 0 \sim 500 \ (V_{CC} = 4.5V) \\ 0 \sim 400 \ (V_{CC} = 6.0V) \end{array}$	ns					

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION		V _{cc}	Ta = 25°C			Ta = -40~85°C		
			Nemen	(V)	MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	VIH			2.0 4.5 6.0	1.50 3.15 4.20			1.50 3.15 4.20		<
Low - Level Input Voltage	VIL			2.0 4.5 6.0			0.50 1.35 1.80		0.50 1.35 1.80	v
High - Level Output Voltage (Qn)	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = — 20µА	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0		1.9 4.4 5.9		v
			$I_{OH} = -4 \text{ mA}$ $I_{OH} = -5.2 \text{ mA}$	4.5 6.0	4.18 5.68	4.31 5.80	-	4.13 5.63	_	
High - Level Output Voltage (ϕ O, ϕ O)	V _{OH}	V _{1N} = V _{1H} or V _{1L}	$I_{OH} = -20 \mu A$	2.0 4.5 6.0	1.8 4.0 5.5	2.0 4.5 5.9		1.8 4.0 5.5		
Low - Level Output Voltage (Qn)	V _{OL}	V _{I N} = V _{I H} or V _{I L}	I _{OL} = 20μA	2.0 4.5 6.0		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	v
			$I_{OL} = 4 \text{ mA}$ $I_{OL} = 5.2 \text{ mA}$	4.5 6.0	-	0.17 0.18	0.26 0.26	-	0.33 0.33	
Low - Level Outpu <u>t</u> Voltage (ϕ O, ϕ O)	V _{OL}	V _{1N} = V _{1H} or V _{1L}	I _{OL} = 20μA	2.0 4.5 6.0		0.0 0.0 0.1	0.2 0.5 0.5		0.2 0.5 0.5	
Input Leakage Current	I _{IN}	$V_{IN} = V_{C}$	6.0	—	_	±0.1	—	± 1.0		
Quiescent Supply Current	I _{cc}	$V_{IN} = V_{C}$	6.0	—	_	4.0	—	40.0	μA	
980508EBA2′										

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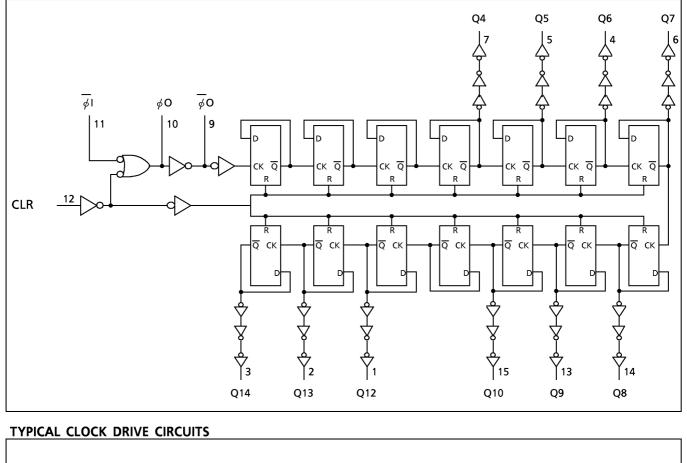
TIMING REQUIREMENTS (Input $t_r = t_f = 6ns$)

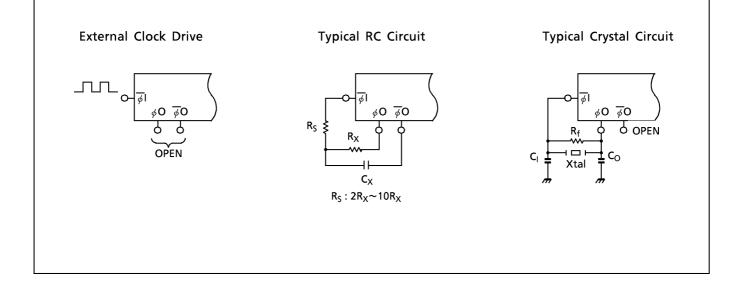
PARAMETER		SYMBOL TEST CONDITION			T	a = 25°	с	Ta = -4	40~85°C	UNIT
FANAIVIETEN				V _{cc} (V)	TYP.			LIMIT		
Minimum Pulse Width (ढ़ा)	t _{W(L)} t _{W(H)}			2.0 4.5 6.0	_ _ _		75 15 13		95 19 16	
Minimum Pulse Time (CLR)	t _{W(H)}			2.0 4.5 6.0			75 15 13	·	95 19 16	ns
Minimum Removal Time	t _{rem}			2.0 4.5 6.0			100 20 17		25 25 21	
Clock Frequency	f			2.0 4.5 6.0	_ _ _		6 30 35		5 24 28	MHz
AC ELECTRICAL CHARACTER	RISTICS (C _L =	= 15pF,V _{cc} = 5V,Ta =	25°C, I	nput t _r	= t _f = 6r	ns)			
PARAMETER	SYMBOL		TEST CONDITION	١	МІ	N.	TYP.	Ν	/IAX.	UNIT
Output Transition Time	t _{TLH} t _{THL}				_		4		8	
Propagation Delay Time $(\overline{\phi}I - Q_4)$	t _{pLH} t _{pHL}				_		36		53	ns
Propagation Delay Time Difference (Qn-Qn+1)	Δt_{pd}		C _L = 50pF (Qn, Qn + 1)		-		6		14	
Propagation Delay Time (CLR)	t _{pHL}				_		19		34	
Maximum Clock Frequency	f _{MAX}				33	3	58		_	MHz
AC ELECTRICAL CHARACTER	RISTICS (C _L =	= 50pF, Input t _r = t _f =	6ns)						
PARAMETER		30L	TEST CONDITION	V _{cc} (V)	T MIN.	a = 25° TYP.	C MAX.	Ta = -4 MIN.	₩ <u>0~85°C</u> MAX.	υνιτ
Output Transition Time	t _{TLI}	I		2.0 4.5 6.0	— — —	30 8 7	75 15 13		95 19 16	
Propagation Delay Time $(\overline{\phi} - Q_4)$		H L		2.0 4.5 6.0		170 41 30	300 60 51		375 75 64	
Propagation Delay Time Difference (Qn-Qn+1)	Δt_{μ}	od	C _L = 50pF(Qn,Qn + 1)	2.0 4.5 6.0		32 7 5	75 15 13		95 19 16	ns
Propagation Delay Time (CLR)	t _{pL} t _{pH}			2.0 4.5 6.0	-	85 23 17	195 39 33		245 49 42	
Maximum Clock Frequency		чX		2.0 4.5 6.0	6 30 35	12 50 65		5 24 28		MHz
Input Capacitance	CIN				_	5	10	_	10	pF
Power Dissipation Capacitance		b	Note (1)		—	27	-		—	

Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC}(opr) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ When CR or Crystal oscillation circuit is adopted, the dynamic power dissipation will be greater than the above calculation, because these oscillation circuits spend much supply current.

TOSHIBA

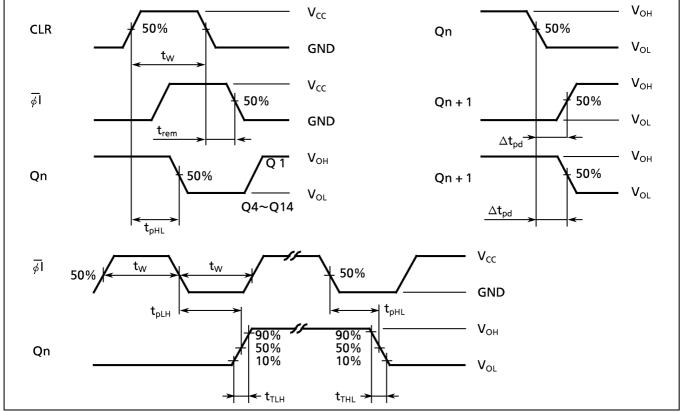
SYSTEM DIAGRAM



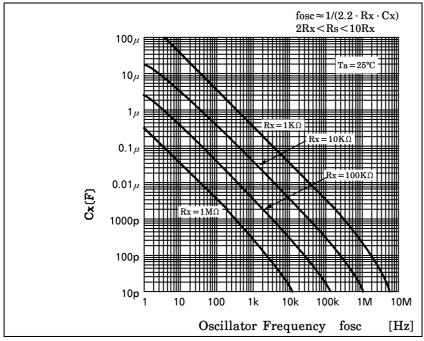


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SWITCHING CHARACTERISTICS TEST WAVEFORM

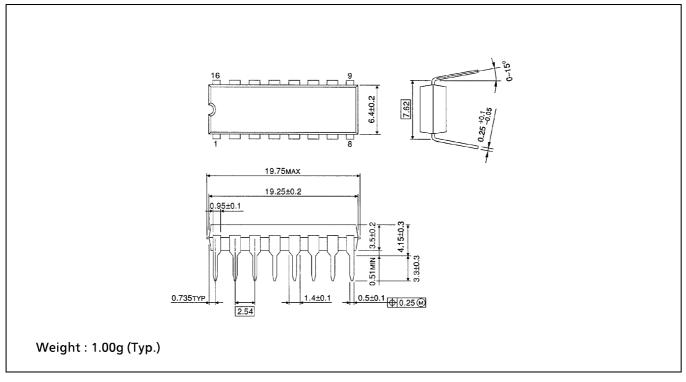


CR Oscillator Characteristics (Typical)



DIP 16PIN OUTLINE DRAWING (DIP16-P-300-2.54A)

Unit in mm



SOP 16PIN (200mil BODY) OUTLINE DRAWING (SOP16-P-300-1.27)

Unit in mm

